US 20240213316A1

(19) United States

(12) Patent Application Publication (10) Pub. No.: US 2024/0213316 A1

JHAN et al. (43) Pub. Date: Jun. 27, 2024

(54) SEMICONDUCTOR DEVICE STRUCTURE AND METHODS OF FORMING THE SAME

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(21) Appl. No.: **18/100,714**

(22) Filed: **Jan. 24, 2023**

Related U.S. Application Data

(60) Provisional application No. 63/435,497, filed on Dec. 27, 2022.

Publication Classification

(51) **Int. Cl.**

H01L 29/06	(2006.01)
H01L 21/8234	(2006.01)
H01L 29/423	(2006.01)
H01L 29/66	(2006.01)
H01L 29/786	(2006.01)

(52) **U.S. Cl.**

CPC .. ***H01L 29/0673*** (2013.01); ***H01L 21/823412*** (2013.01); ***H01L 21/823418*** (2013.01); ***H01L 21/823481*** (2013.01); ***H01L 29/42392*** (2013.01); ***H01L 29/66545*** (2013.01); ***H01L 29/78696*** (2013.01)

(57) **ABSTRACT**

A method for forming a nanosheet device is provided. The method includes epitaxially growing a conformal semiconductor layer from a first stack of semiconductor layers and a second stack of the semiconductor layers. Each of the first and second stack of semiconductor layers includes a plurality of first semiconductor layers and a plurality of second semiconductor layers alternately stacked on each other. A space between the first and second stacks of semiconductor layers is filled with a dielectric fin. The conformal semiconductor layer and the second semiconductor layers may be removed. A metal gate structure is formed over the first semiconductor layers and filling openings created by removal of the conformal semiconductor layer and the second semiconductor layer. A process may be performed on the metal gate structure to form an isolation between the portions of the metal gate structure being separated by a patterning process.